N- and P-Channel 40-V (D-S) MOSFET

PRODUCT SUMMARY				
	V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)[a]	Q_g (Typ)
N-Channel	40	0.027 at V_{GS} = 10 V	6.0	9.6
		0.032 at V_{GS} = 4.5 V	4.8	
P-Channel	–40	0.029 at V_{GS} = –10 V	–6.0	21
		0.039 at V_{GS} = –4.5 V	–4.9	

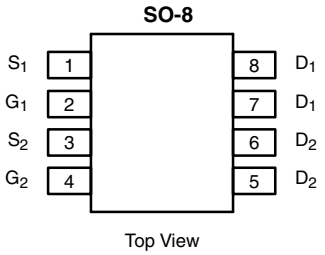
FEATURES

- TrenchFET® Power MOSFET
- 100 % R_g and UIS Tested

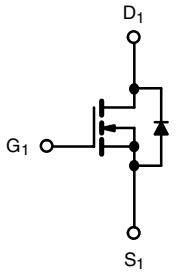
APPLICATIONS

- CCFL Inverter

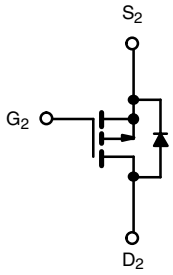
Pb-free
RoHS COMPLIANT



Top View



N-Channel MOSFET



P-Channel MOSFET

Ordering Information: Si4569DY-T1—E3 (Lead (Pb)-free)

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C UNLESS OTHERWISE NOTED)					
Parameter		Symbol	N-Channel	P-Channel	Unit
Drain-Source Voltage		V_{DS}	40	–40	V
Gate-Source Voltage		V_{GS}	± 16		
Continuous Drain Current (T_J = 150 °C)	T_C = 25 °C	I_D	7.6	–7.9	A
	T_C = 70 °C		6.0	–6.3	
	T_A = 25 °C		6.0[b, c]	–6.1[b, c]	
	T_A = 70 °C		4.8[b, c]	–4.9[b, c]	
Pulsed Drain Current (10 μs Pulse Width)		I_{DM}	20	–20	
Source-Drain Current Diode Current	T_C = 25 °C	I_S	2.6	–2.6	
	T_A = 25 °C		1.6[b, c]	–1.6[b, c]	
Pulsed Source-Drain Current		I_{SM}	20	–20	
Single Pulse Avalanche Current	L = 0.1 mH	I_{AS}	10	20	
Single Pulse Avalanche Energy		E_{AS}	5	20	mJ
Maximum Power Dissipation	T_C= 25 °C	P_D	3.1	3.2	W
	T_C= 70 °C		2	2.1	
	T_A = 25 °C		2[b, c]	2[b, c]	
	T_A = 70 °C		1.28[b, c]	1.28[b, c]	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	–55 to 150		°C

THERMAL RESISTANCE RATINGS							
			N-Channel		P-Channel		
Parameter		Symbol	Typ	Max	Typ	Max	Unit
Maximum Junction-to-Ambient[b, d]	t ≤ 10 sec	R_{thJA}	49	62.5	47	62.5	°C/W
Maximum Junction-to-Foot (Drain)	Steady-State	R_{thJF}	30	40	29	38	

Notes
a. Based on T_C = 25 °C.
b. Surface Mounted on 1" x 1" FR4 Board.
c. t = 10 sec.
d. Maximum under steady state conditions is 120 °C/W (n-channel) and 110 °C/W (p-channel).

SPECIFICATIONS (T_J = 25 °C UNLESS OTHERWISE NOTED)

Parameter	Symbol	Test Condition		Min	Typ[a]	Max	Unit
Static							
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = 250 μA	N-Ch	40			V
		V_{GS} = 0 V, I_D = –250 μA	P-Ch	–40			
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	I_D = 250 μA	N-Ch		37		
		I_D = –250 μA	P-Ch		–38		
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	I_D = 250 μA	N-Ch		–5		
		II_D = –250 μA	P-Ch		4.0		
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 μA	N-Ch	0.6		2.0	
		V_{DS} = V_{GS}, I_D = –250 μA	P-Ch	–0.8		–2.2	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 16 V	N-Ch			100	nA
			P-Ch			–100	
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 40 V, V_{GS} = 0 V	N-Ch			1	μA
		V_{DS} = –40 V, V_{GS} = 0 V	P-Ch			–1	
		V_{DS} = 40 V, V_{GS} = 0 V, T_J = 55 °C	N-Ch			10	
		V_{DS} = –40 V, V_{GS} = 0 V, T_J = 55 °C	P-Ch			–10	
On-State Drain Current[b]	$I_{D(on)}$	V_{DS} = 5 V, V_{GS} = 10 V	N-Ch	20			A
		V_{DS} = –5 V, V_{GS} = –10 V	P-Ch	–20			
Drain-Source On-State Resistance[b]	$r_{DS(on)}$	V_{GS} = 10 V, I_D = 6 A	N-Ch		0.022	0.027	Ω
		V_{GS} = –10 V, I_D = –6 A	P-Ch		0.024	0.029	
		V_{GS} = 4.5 V, I_D = 4.8 A	N-Ch		0.026	0.032	
		V_{GS} = –4.5 V, I_D = –4.9 A	P-Ch		0.031	0.039	
Forward Transconductance[b]	g_{fs}	V_{DS} = 15 V, I_D = 6 A	N-Ch		20		S
		V_{DS} = –15 V, I_D = –6 A	P-Ch		17		
Dynamic[a]							
Input Capacitance	C_{iss}	N-Channel V_{DS} = 20 V, V_{GS} = 0 V, f = 1 MHz P-Channel V_{DS} = – 20 V, V_{GS} = 0 V, f = 1 MHz	N-Ch		855		pF
			P-CH		1505		
Output Capacitance	C_{oss}		N-Ch		105		
			P-Ch		230		
Reverse Transfer Capacitance	C_{rss}		N-Ch		65		
			P-Ch		175		
Total Gate Charge	Q_g	V_{DS} = 20 V, V_{GS} = 10 V, I_D = 5 A	N-Ch		21	32	nC
		V_{DS} = –20 V, V_{GS} = –10 V, I_D = –5 A	P-Ch		41	62	
		N-Channel V_{DS} = 20 V, V_{GS} = 4.5 V, I_D = 5 A P-Channel V_{DS} = – 20 V, V_{GS} = –4.5 V, I_D = –5 A	N-Ch		9.6	14.5	
			P-Ch		21	31	
Gate-Source Charge	Q_{gs}		N-Ch		2.3		
			P-Ch		4.5		
Gate-Drain Charge	Q_{gd}		N-Ch		3.2		
			P-Ch		9.2		
Gate Resistance	R_g	f = 1 MHz	N-Ch		2.5	3.8	Ω
			P-Ch		6.5	10	

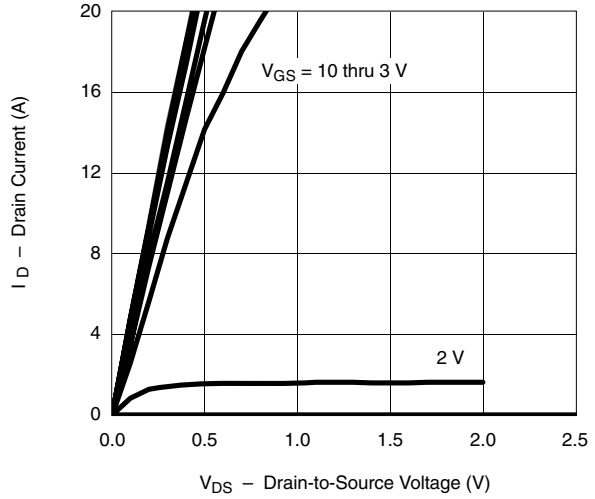
SPECIFICATIONS (T_J = 25 °C UNLESS OTHERWISE NOTED)							
Parameter	**Symbol**	**Test Condition**		**Min**	**Typ[a]**	**Max**	**Unit**
Dynamic[a]							
Turn-On Delay Time	$t_{d(on)}$	N-Channel V_{DD} = 20 V, R_L = 4 Ω I_D ≅ 5 A, V_{GEN} = 10 V, R_g = 1 Ω P-Channel V_{DD} = –20 V, R_L = 4 Ω I_D ≅ –5 A, V_{GEN} = –10 V, R_g = 1 Ω	N-Ch		6	12	ns
			P-Ch		7	14	
Rise Time	t_r		N-Ch		11	20	
			P-Ch		15	25	
Turn-Off Delay Time	$t_{d(off)}$		N-Ch		24	36	
			P-Ch		51	77	
Fall Time	t_f		N-Ch		6	12	
			P-Ch		54	81	
Turn-On Delay Time	$t_{d(on)}$	N-Channel V_{DD} = 20 V, R_L = 4 Ω I_D ≅ 5 A, V_{GEN} = 4.5 V, R_g = 1 Ω P-Channel V_{DD} = –20 V, R_L = 4 Ω I_D ≅ –5 A, V_{GEN} = –4.5 V, R_g =1 Ω	N-Ch		12	20	
			P-Ch		26	40	
Rise Time	t_r		N-Ch		60	90	
			P-Ch		105	160	
Turn-Off Delay Time	$t_{d(off)}$		N-Ch		22	33	
			P-Ch		60	90	
Fall Time	t_f		N-Ch		5	10	
			P-Ch		60	90	
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I_S	T_C = 25 °C	N-Ch			2.6	A
			P-Ch			–2.6	
Pulse Diode Forward Current[a]	I_{SM}		N-Ch			20	
			P-Ch			–20	
Body Diode Voltage	V_{SD}	I_S = 1.5 A	N-Ch		0.73	1.2	V
		I_S = –1.6 A	P-Ch		–0.73	–1.2	
Body Diode Reverse Recovery Time	t_{rr}	N-Channel I_F = 5 A, di/dt = 100 A/µs, T_J = 25 °C P-Channel I_F = –5 A, di/dt = –100 A/µs, T_J = 25 °C	N-Ch		26	40	ns
			P-Ch		30	45	
Body Diode Reverse Recovery Charge	Q_{rr}		N-Ch		21	32	nC
			P-Ch		24	36	
Reverse Recovery Fall Time	t_a		N-Ch		13		ns
			P-Ch		15		
Reverse Recovery Rise Time	t_b		N-Ch		13		
			P-Ch		15		

Notes
a. Guaranteed by design, not subject to production testing.
b. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.

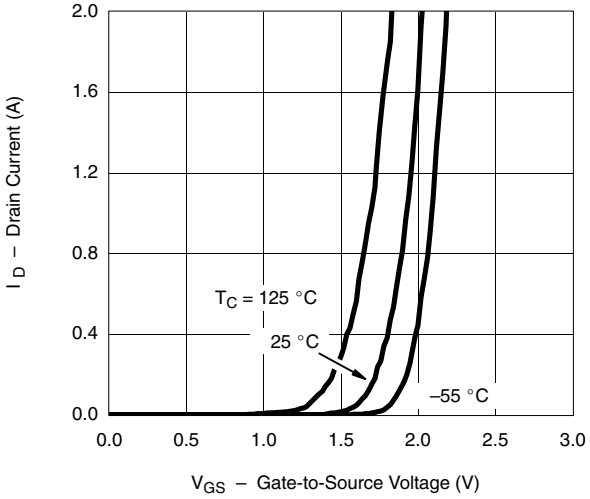
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED) N-CHANNEL

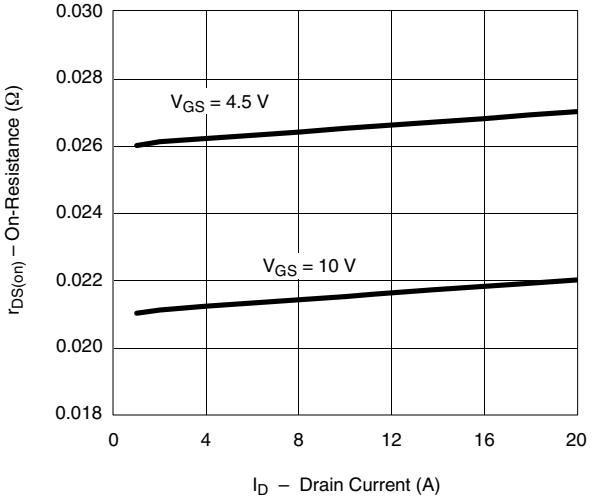
Output Characteristics



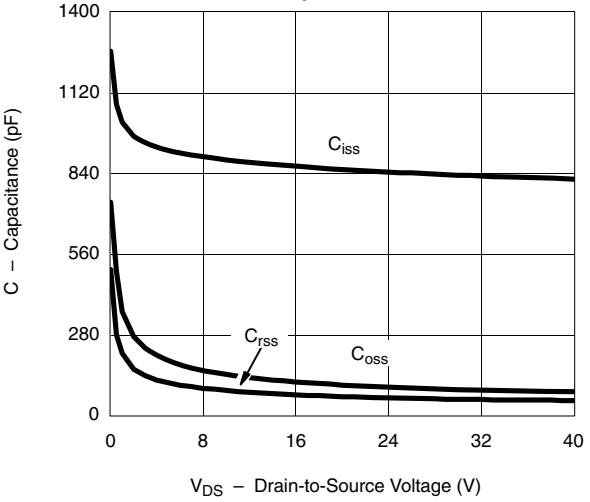
Transfer Characteristics



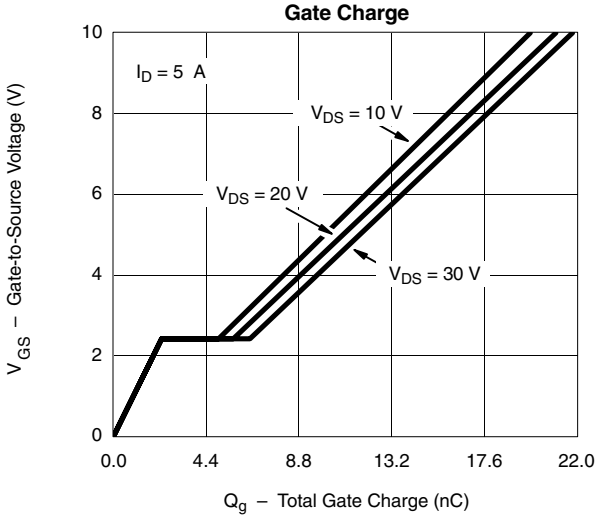
On-Resistance vs. Drain Current and Gate Voltage



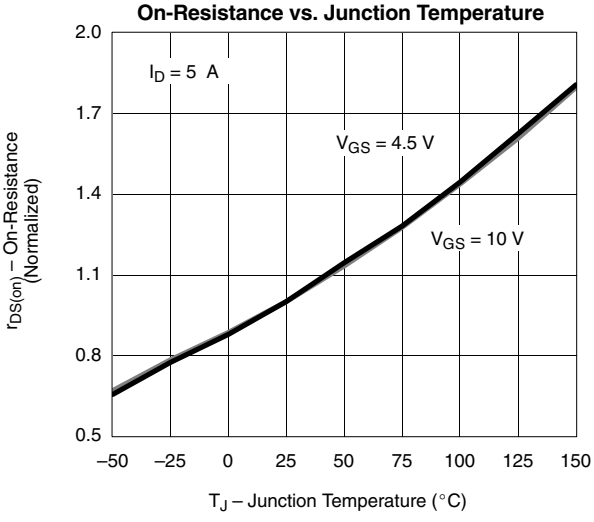
Capacitance



Gate Charge

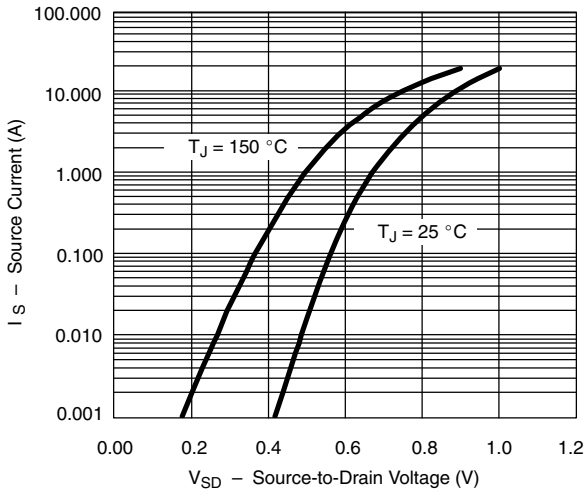


On-Resistance vs. Junction Temperature

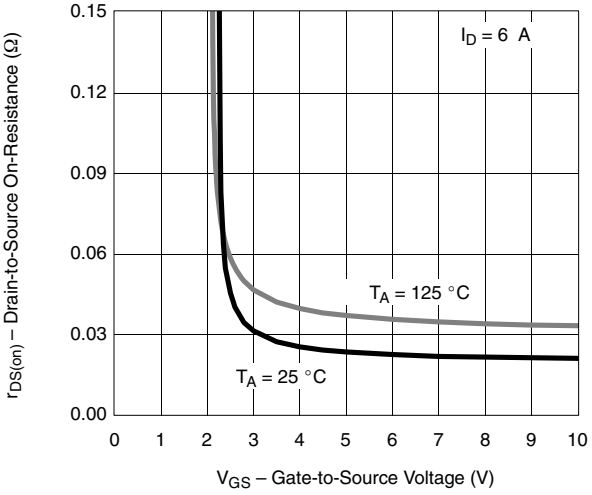


TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED) — N-CHANNEL

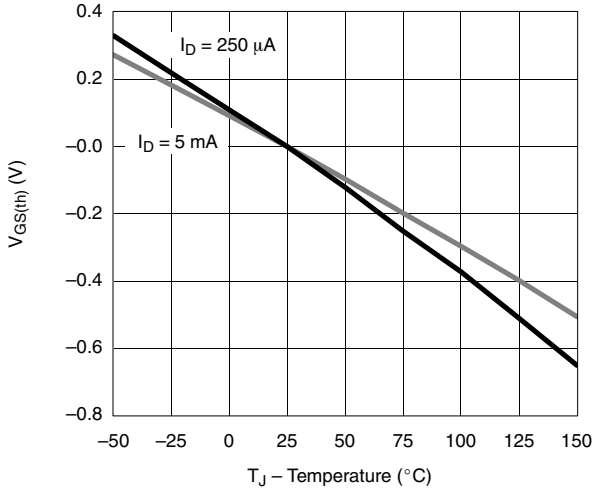
Source-Drain Diode Forward Voltage



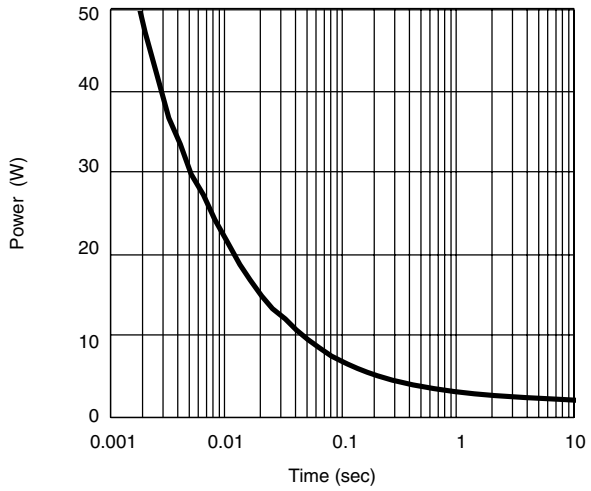
On-Resistance vs. Gate-to-Source Voltage



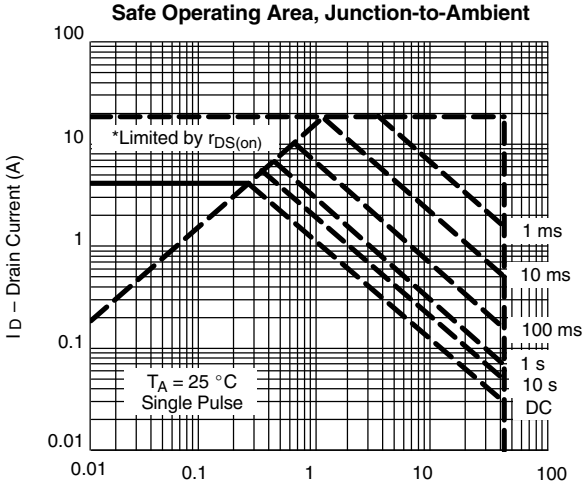
Threshold Voltage



Single Pulse Power, Junction-to-Ambient



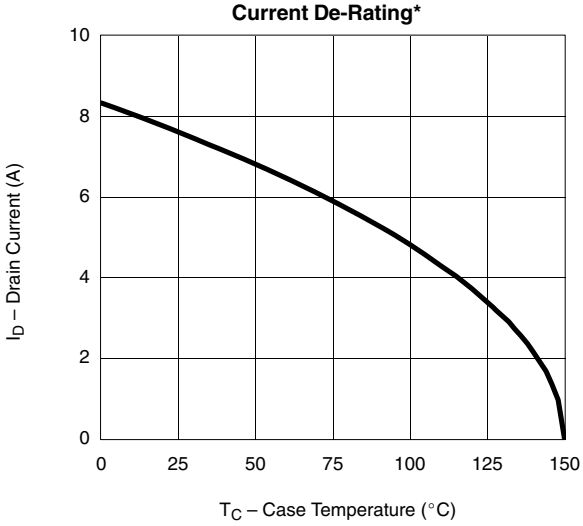
Safe Operating Area, Junction-to-Ambient



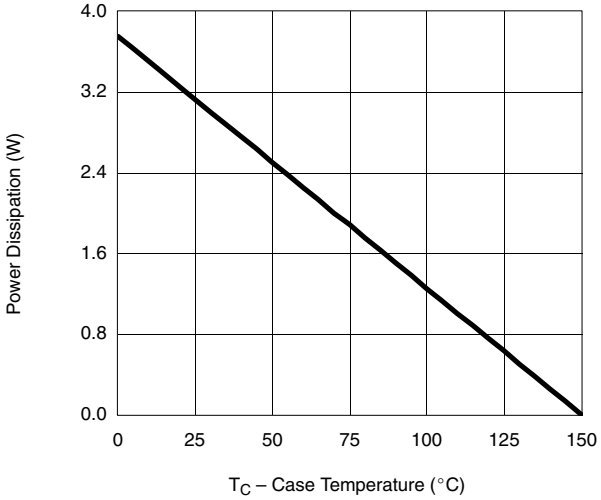
*V_{GS} > minimum V_{GS} at which $r_{DS(on)}$ is specified

TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED) N-CHANNEL

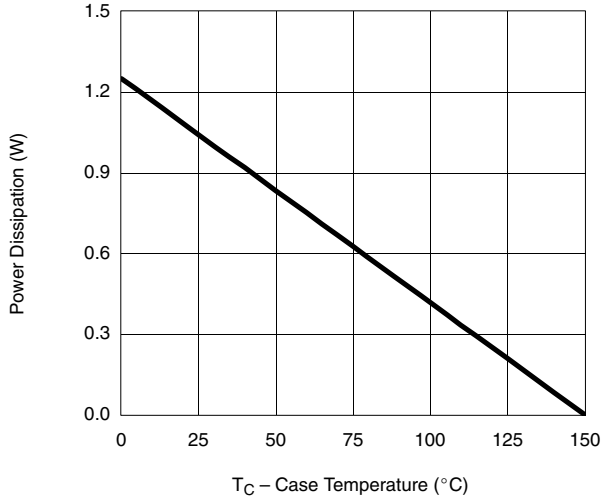
Current De-Rating*



Power De-Rating, Junction-to-Foot



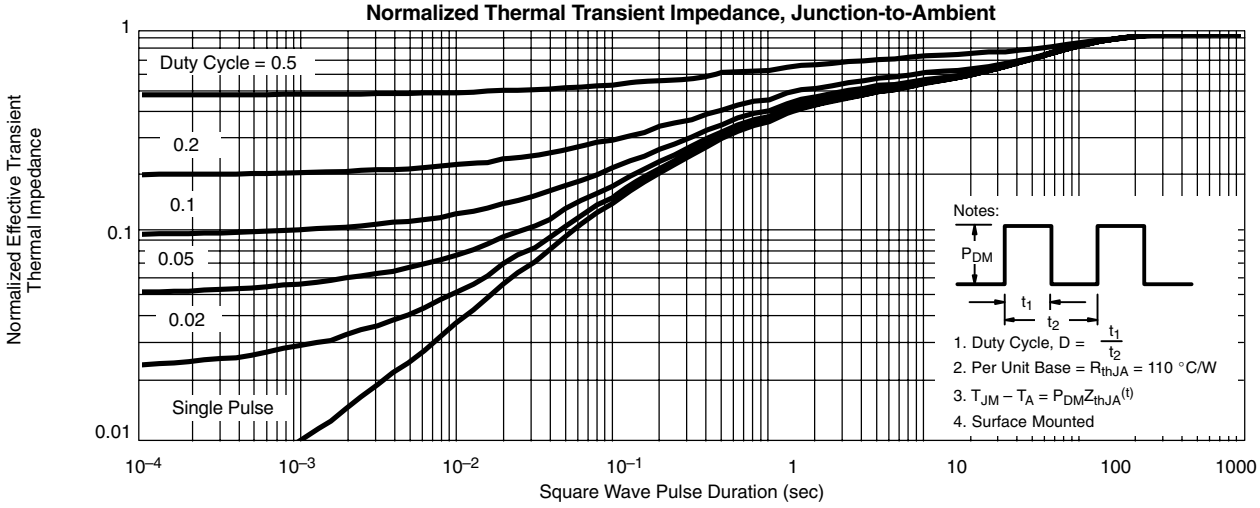
Power De-Rating, Junction-to-Ambient



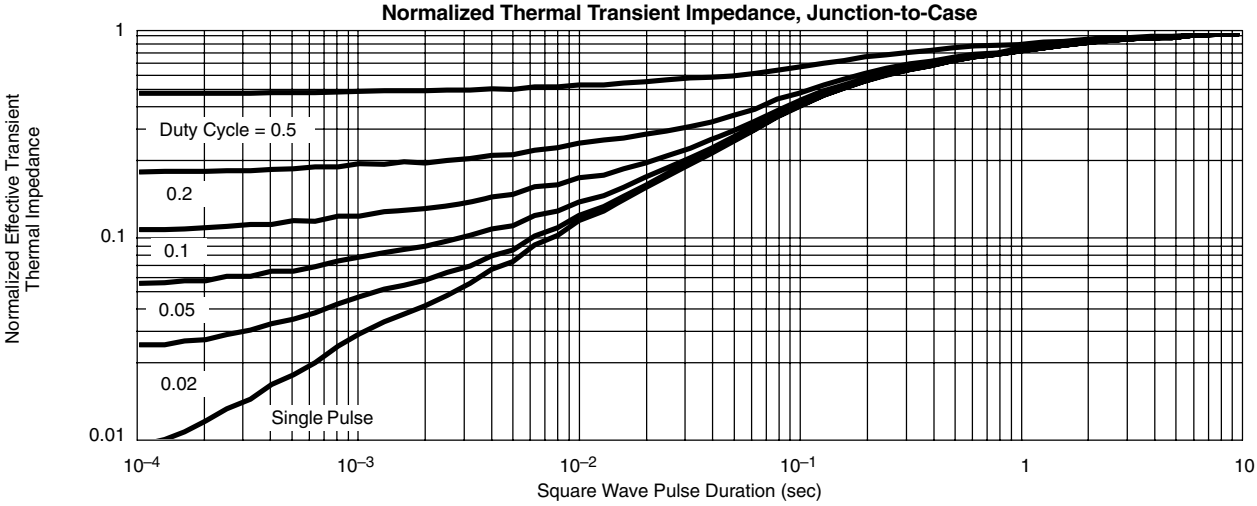
*The power dissipation P_b is based on $T_{J(max)}$ = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED) N-CHANNEL

Normalized Thermal Transient Impedance, Junction-to-Ambient

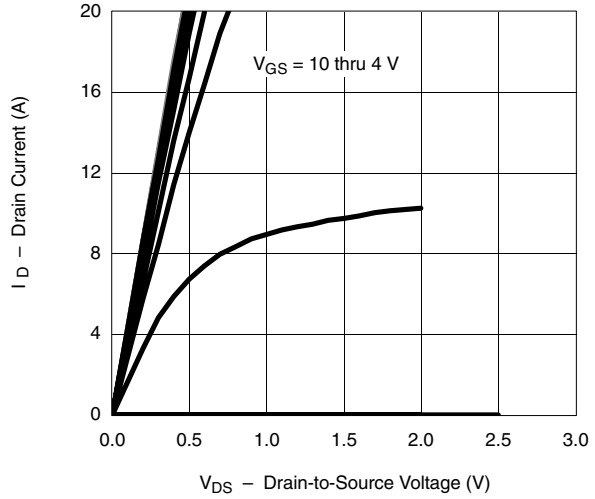


Normalized Thermal Transient Impedance, Junction-to-Case

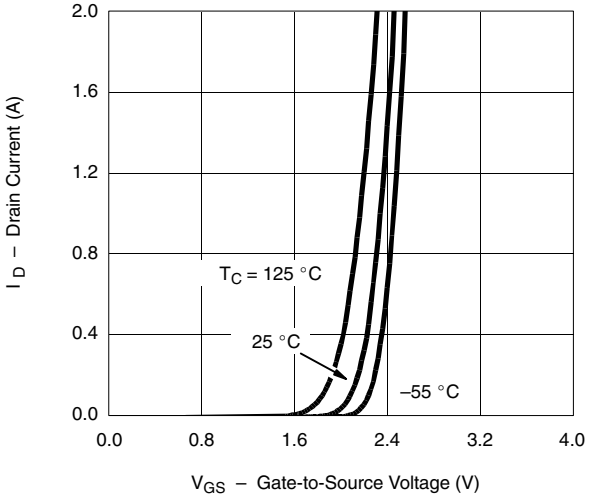


TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED) P-CHANNEL

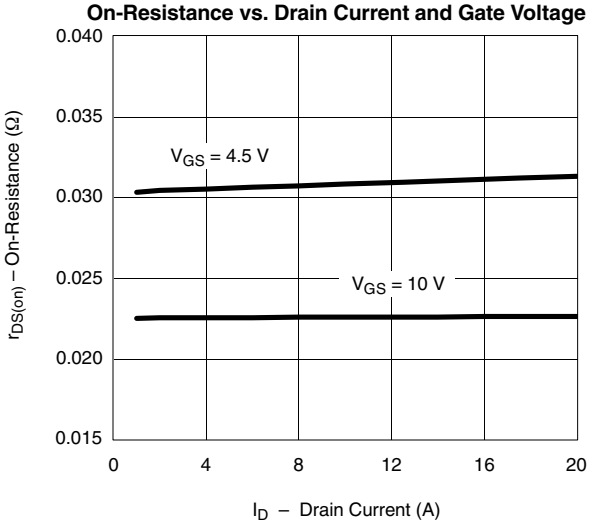
Output Characteristics



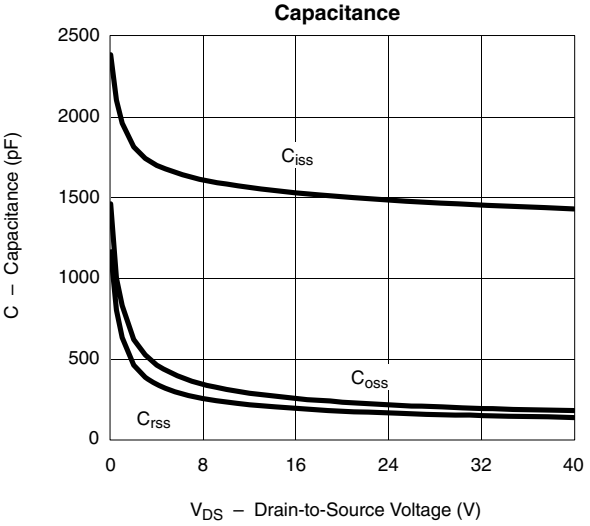
Transfer Characteristics



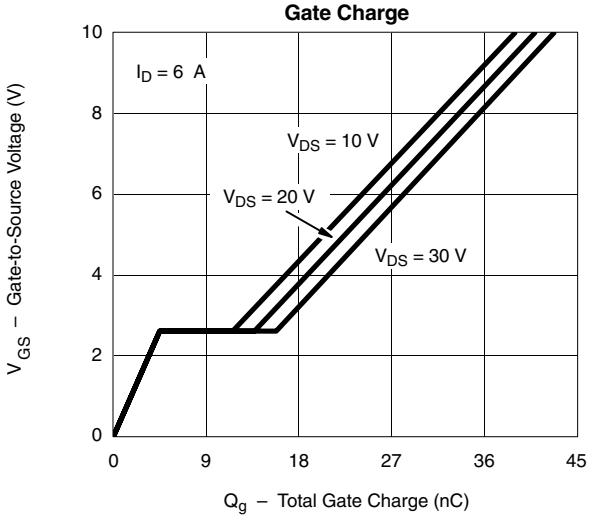
On-Resistance vs. Drain Current and Gate Voltage



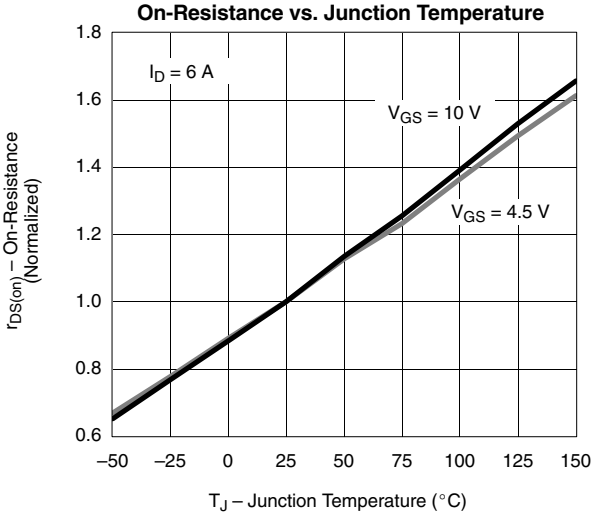
Capacitance



Gate Charge

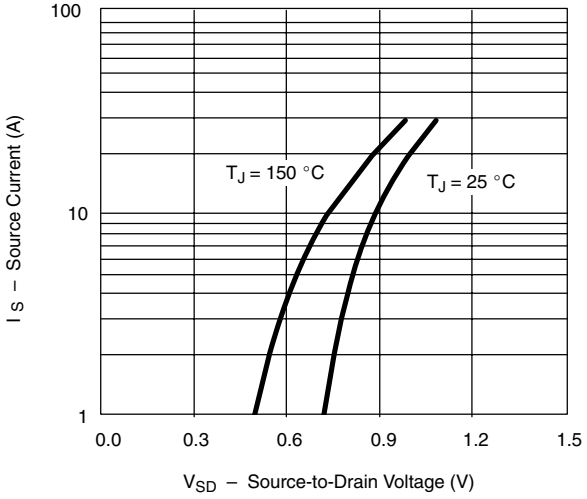


On-Resistance vs. Junction Temperature

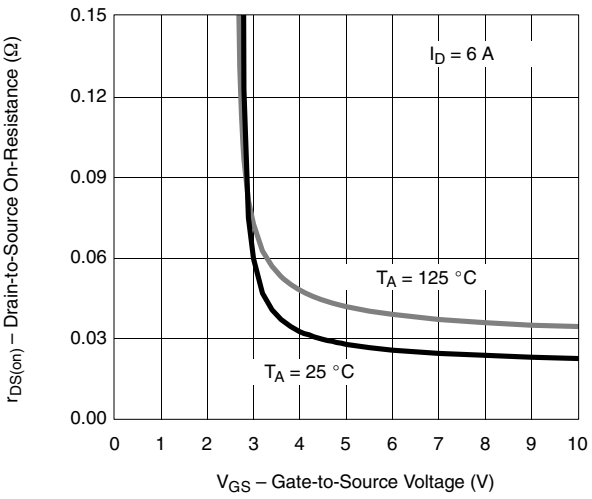


TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED) P-CHANNEL

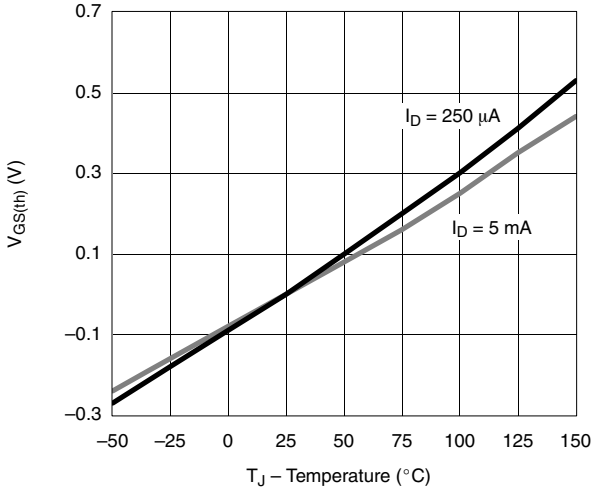
Source-Drain Diode Forward Voltage



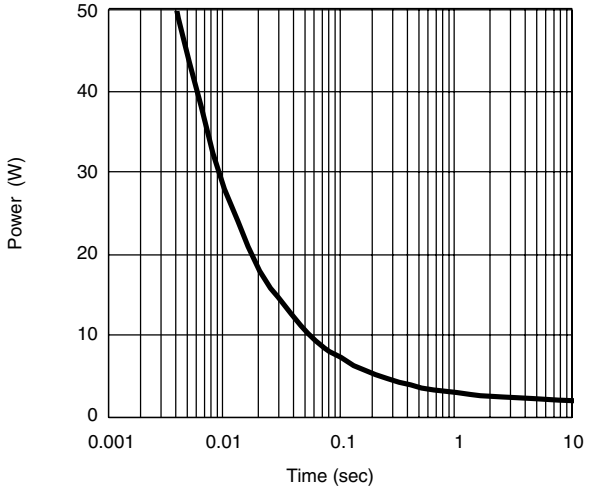
On-Resistance vs. Gate-to-Source Voltage



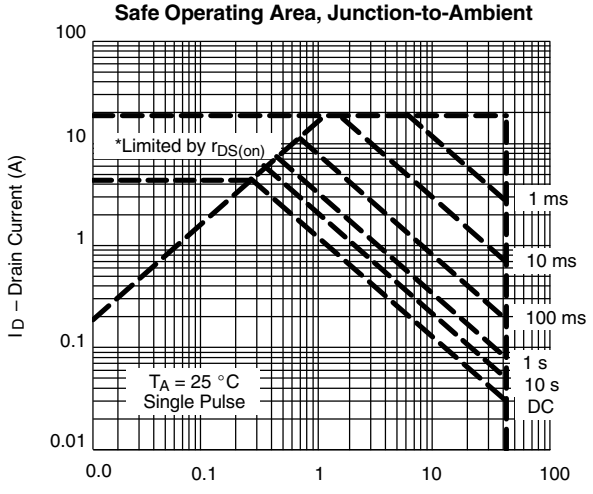
Threshold Voltage



Single Pulse Power, Junction-to-Ambient



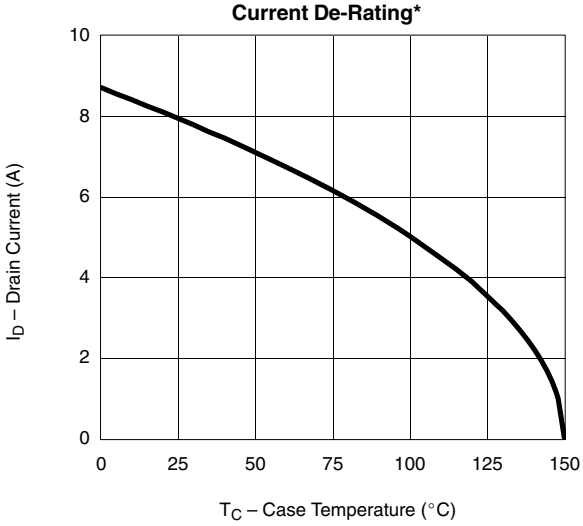
Safe Operating Area, Junction-to-Ambient



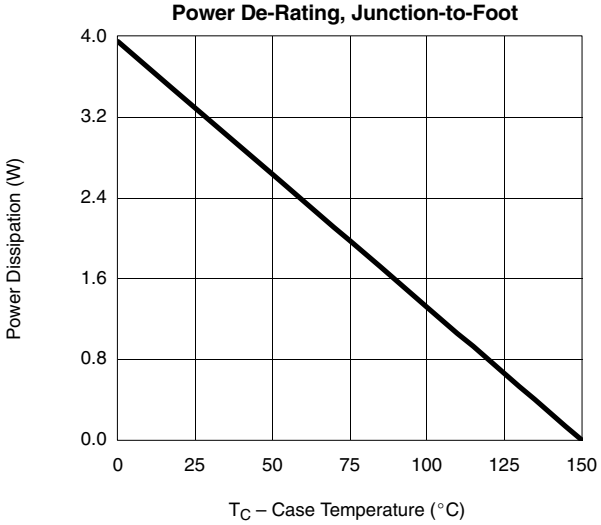
*V_{GS} > minimum V_{GS} at which $r_{DS(on)}$ is specified

TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED) P-CHANNEL

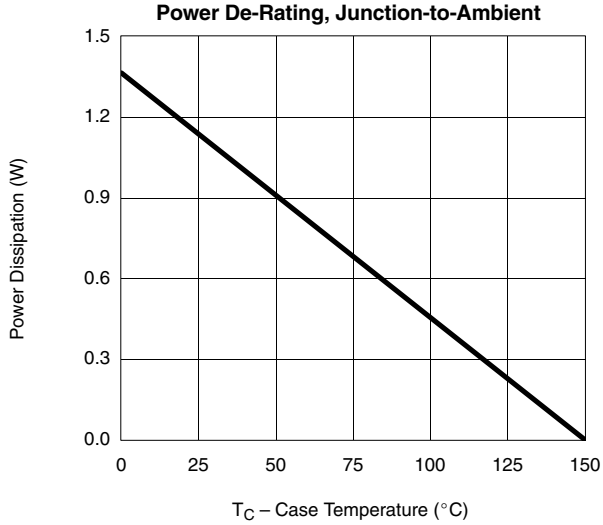
Current De-Rating*



Power De-Rating, Junction-to-Foot

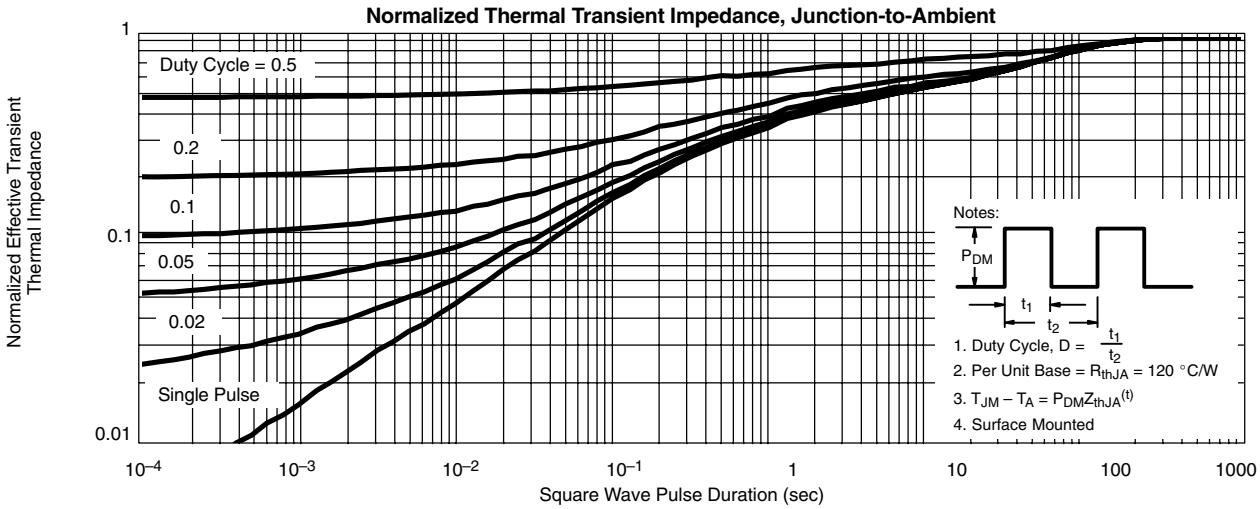


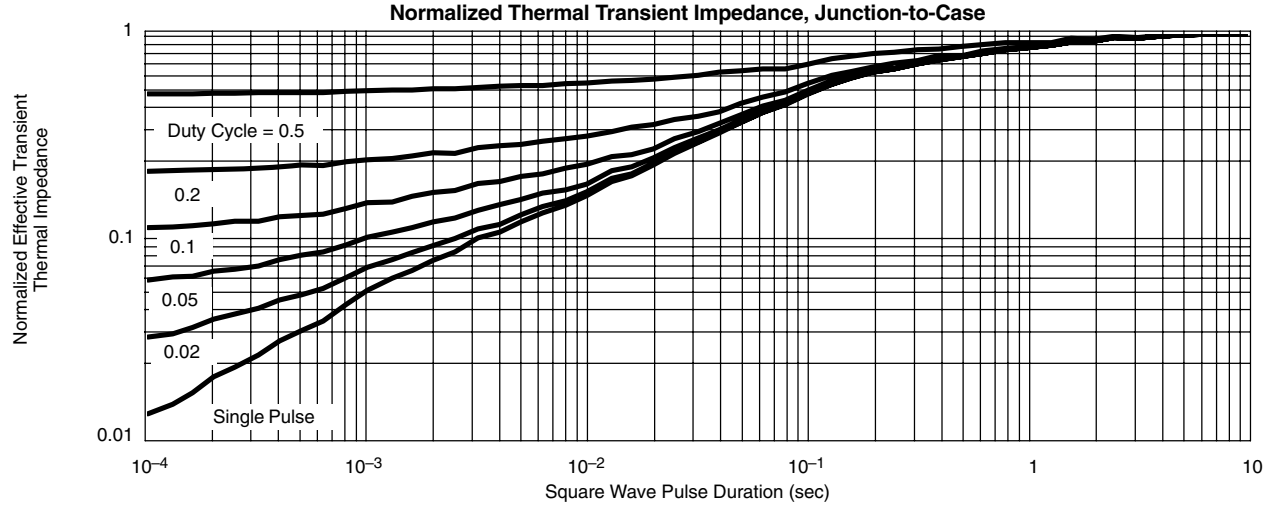
Power De-Rating, Junction-to-Ambient



*The power dissipation P_b is based on $T_{J(max)}$ = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED) P-CHANNEL





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